

30V N+N-channel SGT MOSFET

DESCRIPTION

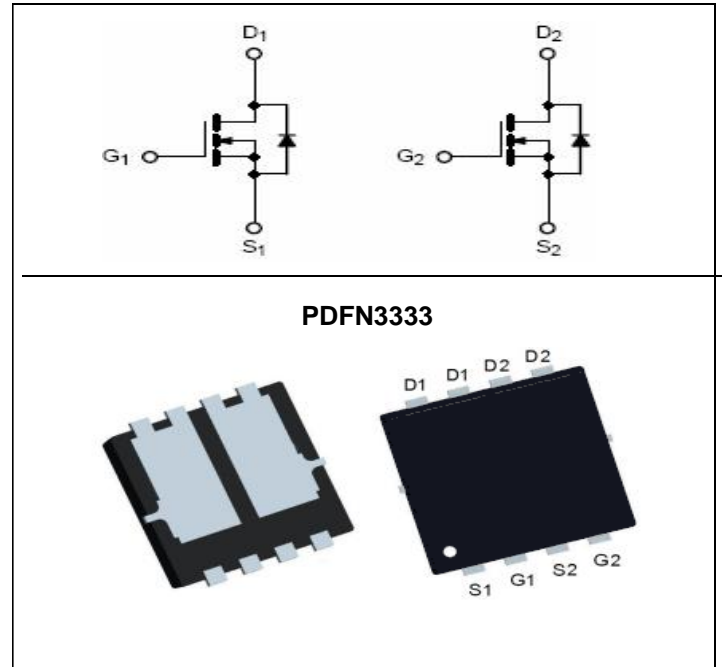
The CX3622DE uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- $R_{DS(ON)} < 10m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(ON)} < 13m\Omega$ @ $V_{GS} = 4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



■ Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_C = 25^\circ C$	I_D	35	A
	$T_C = 100^\circ C$		22	
Pulsed Drain Current ^A		I_{DM}	140	A
Total Power Dissipation	$T_C = 25^\circ C$	P_D	20	W
	$T_C = 100^\circ C$		15	W
Single Pulse Avalanche Energy ^B		E_{AS}	16	mJ
Thermal Resistance Junction-to-Case ^C		$R_{\theta JC}$	45	$^\circ C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55 ~ +155	$^\circ C$